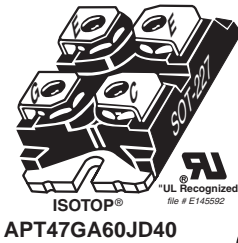


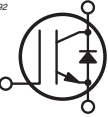
High Speed PT IGBT

POWER MOS 8® is a high speed Punch-Through switch-mode IGBT. Low E_{off} is achieved through leading technology silicon design and lifetime control processes. A reduced $E_{off} - V_{CE(ON)}$ tradeoff results in superior efficiency compared to other IGBT technologies. Low gate charge and a greatly reduced ratio of C_{res}/C_{ies} provide excellent noise immunity, short delay times and simple gate drive. The intrinsic chip gate resistance and capacitance of the poly-silicone gate structure help control di/dt during switching, resulting in low EMI, even when switching at high frequency.




ISOTOP®
APT47GA60JD40

Combi (IGBT and Diode)



FEATURES

- Fast switching with low EMI
- Very Low E_{off} for maximum efficiency
- Ultra low C_{res} for improved noise immunity
- Low conduction loss
- Low gate charge
- Increased intrinsic gate resistance for low EMI
- RoHS compliant 

TYPICAL APPLICATIONS

- ZVS phase shifted and other full bridge
- Half bridge
- High power PFC boost
- Welding
- UPS, solar, and other inverters
- High frequency, high efficiency industrial

Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V_{CES}	Collector Emitter Voltage	600	V
I_{C1}	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	87	A
I_{C2}	Continuous Collector Current @ $T_C = 100^\circ\text{C}$	47	
I_{CM}	Pulsed Collector Current ¹	139	
V_{GE}	Gate-Emitter Voltage ²	± 30	V
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	283	W
SSOA	Switching Safe Operating Area @ $T_J = 150^\circ\text{C}$	139A @ 600V	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Lead Temperature for Soldering: 0.063" from Case for 10 Seconds	300	

Static Characteristics

$T_J = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{BR(CES)}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 1.0mA$	600			V
$V_{CE(on)}$	Collector-Emitter On Voltage	$V_{GE} = 15V, I_C = 47A$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		2.0 1.9	2.5	
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1mA$	3	4.5	6	
I_{CES}	Zero Gate Voltage Collector Current	$V_{CE} = 600V, V_{GE} = 0V$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			275 3000	μA
I_{GES}	Gate-Emitter Leakage Current	$V_{GS} = \pm 30V$			± 100	nA

Dynamic Characteristics

$T_J = 25^\circ\text{C}$ unless otherwise specified

APT47GA60JD40

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit	
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1\text{MHz}$		6320		pF	
C_{oes}	Output Capacitance			580			
C_{res}	Reverse Transfer Capacitance			63			
Q_g^3	Total Gate Charge	Gate Charge $V_{GE} = 15V$ $V_{CE} = 300V$ $I_C = 47A$		226		nC	
Q_{ge}	Gate-Emitter Charge			46			
Q_{gc}	Gate- Collector Charge			78			
SSOA	Switching Safe Operating Area	$T_J = 150^\circ\text{C}, R_G = 10\Omega^4, V_{GE} = 15V,$ $L = 100\mu\text{H}, V_{CE} = 600V$	139			A	
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (25°C) $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 47A$ $R_G = 4.7\Omega^4$ $T_J = +25^\circ\text{C}$		24		ns	
t_r	Current Rise Time			26			
$t_{d(off)}$	Turn-Off Delay Time			158			
t_f	Current Fall Time			56			
E_{on2}	Turn-On Switching Energy	Inductive Switching (125°C) $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 47A$ $R_G = 4.7\Omega^4$ $T_J = +125^\circ\text{C}$		1119		μJ	
E_{off}^6	Turn-Off Switching Energy			693			
$t_{d(on)}$	Turn-On Delay Time			23			ns
t_r	Current Rise Time			28			
$t_{d(off)}$	Turn-Off Delay Time		190				
t_f	Current Fall Time		109				
E_{on2}	Turn-On Switching Energy			1984		μJ	
E_{off}^6	Turn-Off Switching Energy			1037			

Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance (IGBT)	-	-	.44	$^\circ\text{C/W}$
$R_{\theta JC}$	Junction to Case Thermal Resistance (Diode)			.67	
W_T	Package Weight	-	29.2	-	g
$V_{Isolation}$	RMS Voltage (50-60Hz Sinusoidal Waveform from Terminals to Mounting Base for 1 Min.)	2500			in-lbf

- 1 Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.
 - 2 Pulse test: Pulse Width < $380\mu\text{s}$, duty cycle < 2%.
 - 3 See Mil-Std-750 Method 3471.
 - 4 R_G is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)
 - 5 E_{on2} is the clamped inductive turn on energy that includes a commutating diode reverse recovery current in the IGBT turn on energy loss. A combi device is used for the clamping diode.
 - 6 E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1.
- Microsemi reserves the right to change, without notice, the specifications and information contained herein.**

ULTRAFAST SOFT RECOVERY RECTIFIER DIODE

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT47GA60JD40	Unit
$I_{F(AV)}$	Maximum Average Forward Current ($T_C = 100^\circ\text{C}$, Duty Cycle = 0.5)	30	Amps
$I_{F(RMS)}$	RMS Forward Current (Square wave, 50% duty)	42	
I_{FSM}	Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3 ms)	320	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	Min	Type	Max	Unit
V_F	Forward Voltage		$I_F = 50\text{A}$	2.1	Volts
			$I_F = 100\text{A}$	2.6	
			$I_F = 50\text{A}, T_J = 125^\circ\text{C}$	1.75	

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
t_{rr}	Reverse Recovery Time	$I_F = 1\text{A}, di_F/dt = -100\text{A}/\mu\text{s}, V_R = 30\text{V}, T_J = 25^\circ\text{C}$	-	21	-	ns
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 25^\circ\text{C}$	-	105	-	ns
Q_{rr}	Reverse Recovery Charge		-	115	-	
I_{RRM}	Maximum Reverse Recovery Current		-	3	-	
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 125^\circ\text{C}$	-	125	-	ns
Q_{rr}	Reverse Recovery Charge		-	465	-	
I_{RRM}	Maximum Reverse Recovery Current		-	7	-	
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -1000\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 125^\circ\text{C}$	-	60	-	ns
Q_{rr}	Reverse Recovery Charge		-	830	-	
I_{RRM}	Maximum Reverse Recovery Current		-	23	-	

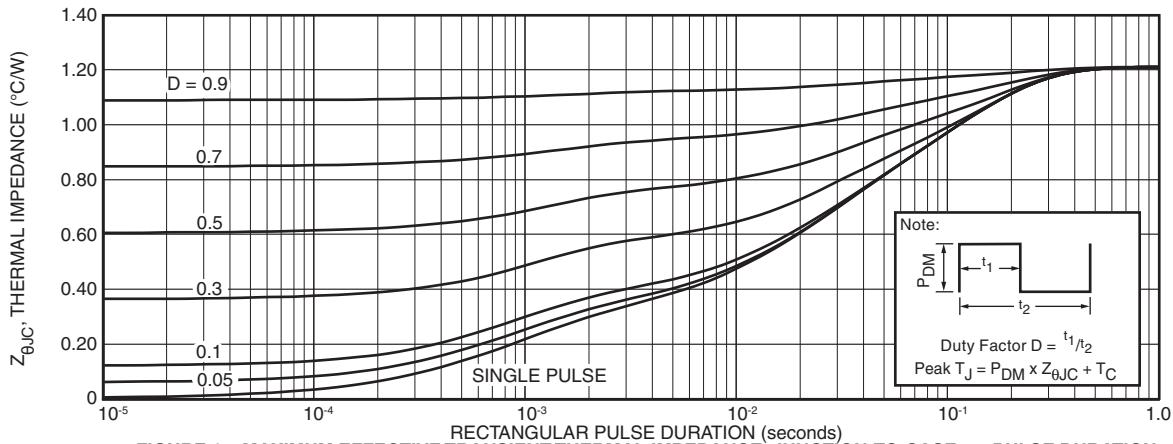


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

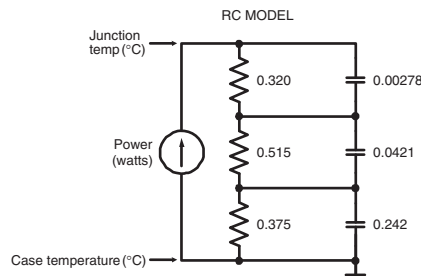


FIGURE 1b. TRANSIENT THERMAL IMPEDANCE MODEL

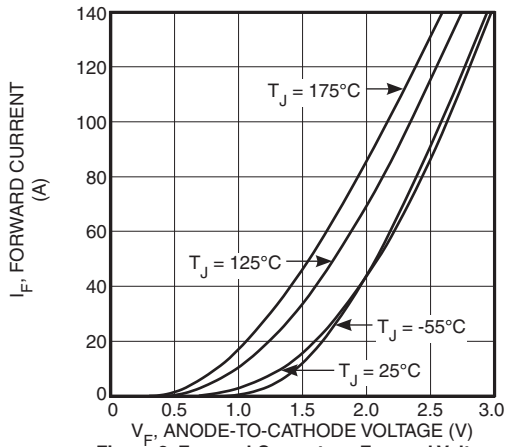


Figure 2. Forward Current vs. Forward Voltage

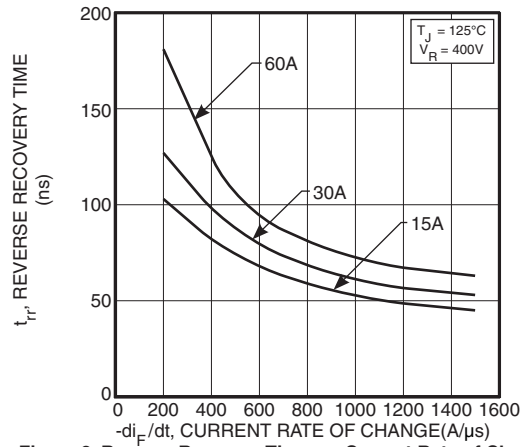


Figure 3. Reverse Recovery Time vs. Current Rate of Change

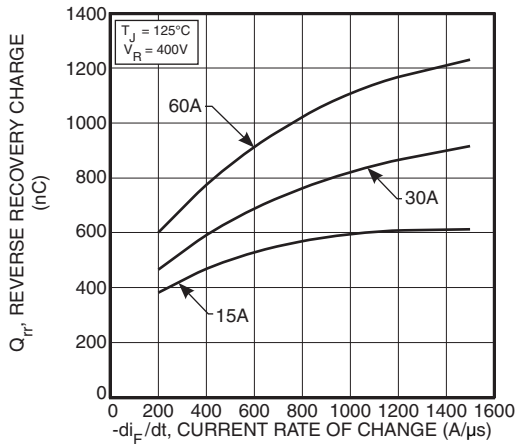


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

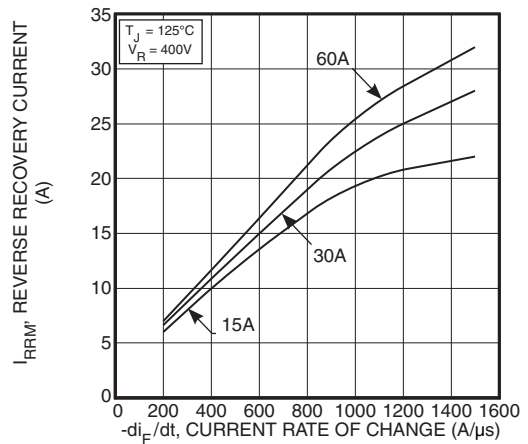


Figure 5. Reverse Recovery Current vs. Current Rate of Change

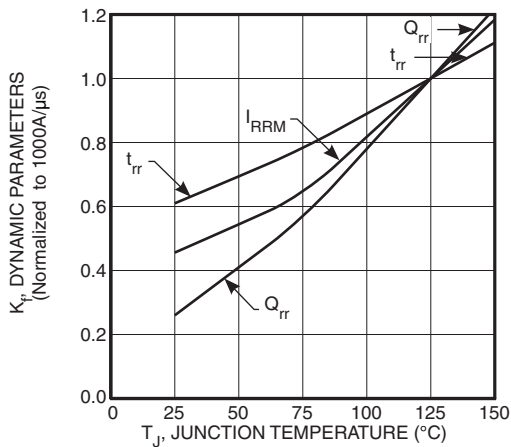


Figure 6. Dynamic Parameters vs. Junction Temperature

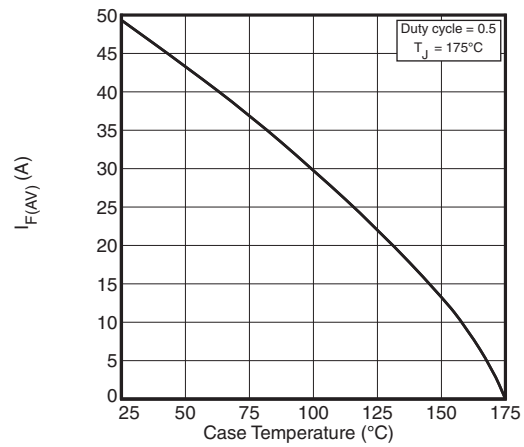


Figure 7. Maximum Average Forward Current vs. Case Temperature

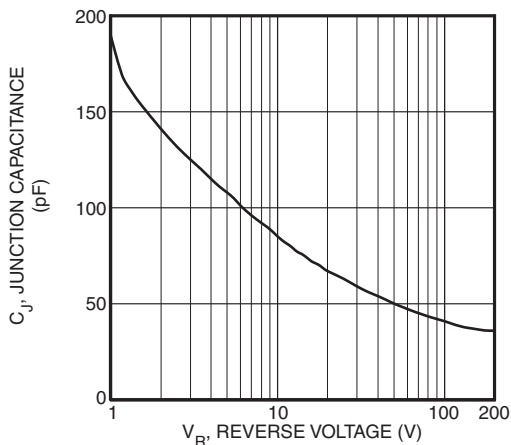


Figure 8. Junction Capacitance vs. Reverse Voltage

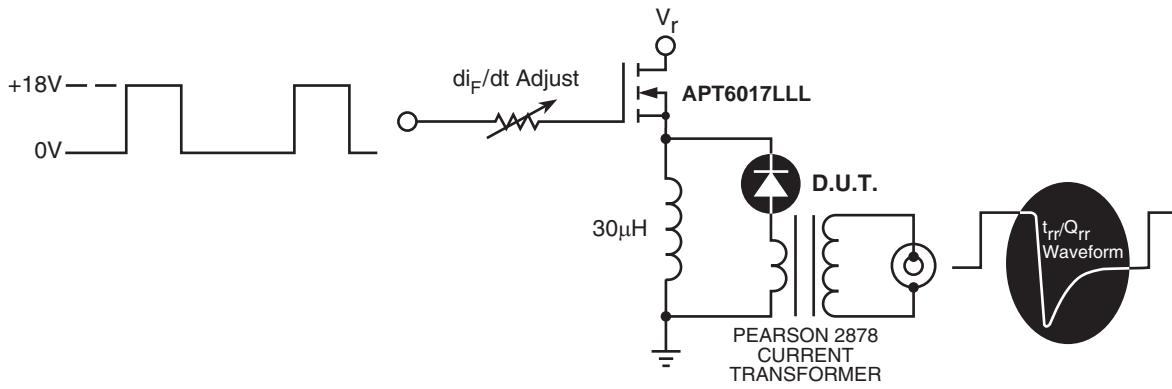


Figure 9, Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{R_{RRM}} - Maximum Reverse Recovery Current.
- 4 t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{R_{RRM}} and 0.25•I_{R_{RRM}} passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{R_{RRM}} and t_{rr}.

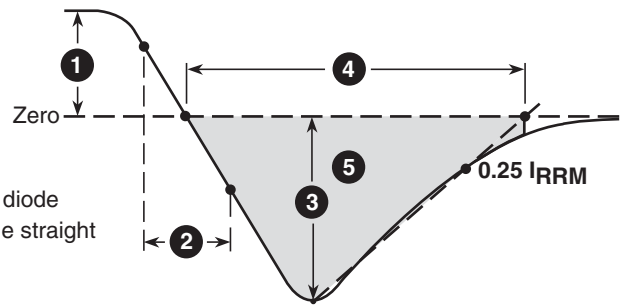
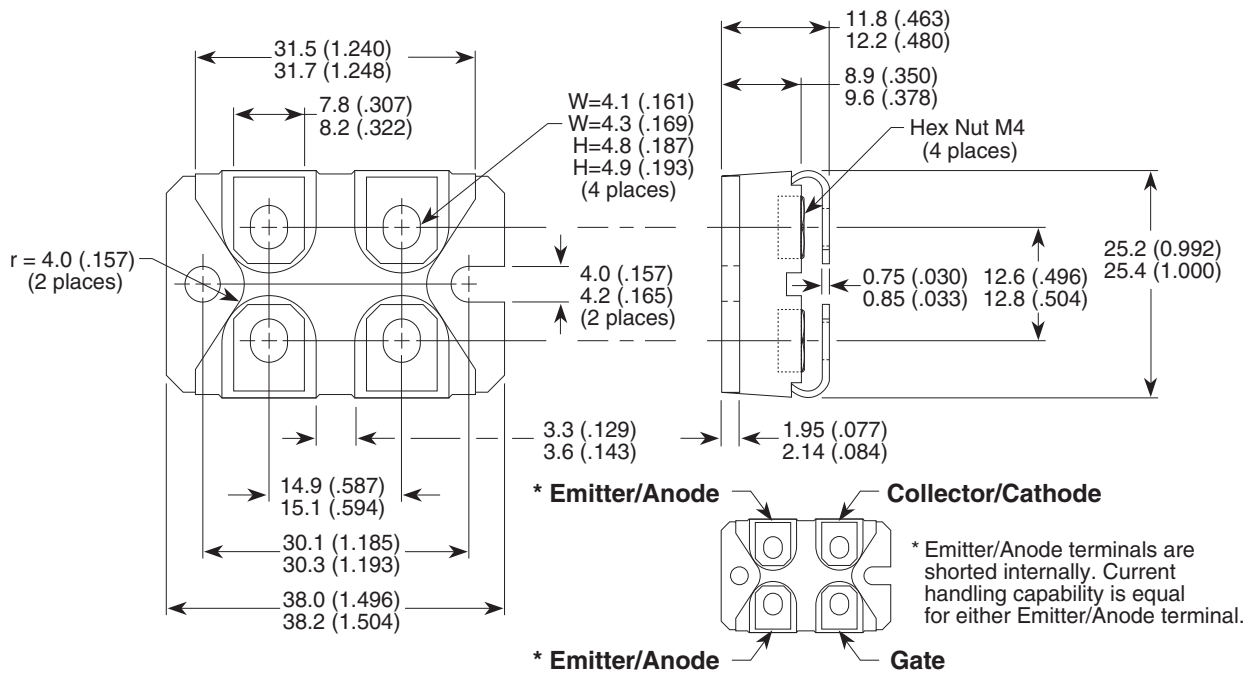


Figure 10, Diode Reverse Recovery Waveform and Definitions

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743, 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. US and Foreign patents pending. All Rights Reserved.